PROCESSING METHOD, METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE, PROCESSING APPARATUS, AND PROGRAM

ABSTRACT

There is provided a technique that includes: forming a film in a recess on a surface of a substrate by performing a cycle n times (where n is an integer of 1 or 2 or more), the cycle including: (a) exposing the substrate to an altering agent excited into a plasma state; (b) exposing the substrate after (a) to an oxygen-containing substance; (c) exposing the substrate after (b) to a modifying agent; and (d) exposing the substrate after (c) to a film-forming agent.

Fig. 1